

Fig. 1A formation of base insulating film/ formation of semiconductor film

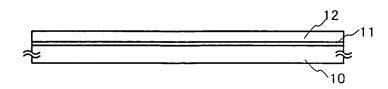


Fig. 1B laser anneal

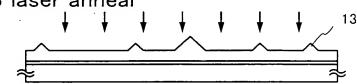


Fig. 1C heat treatment process

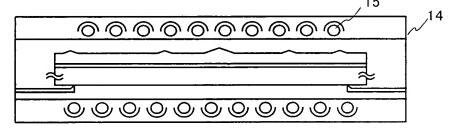
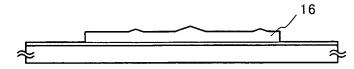


Fig. 1D formation of semiconductor film



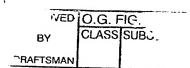


Fig. 2A formation of base insulating film/ formation of semiconductor film

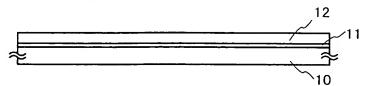


Fig. 2B laser anneal

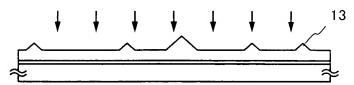


Fig. 2C formation of semiconductor film



Fig. 2D heat treatment process

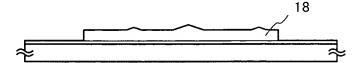


Fig. 3A formation of base insulating film/ formation of semiconductor film

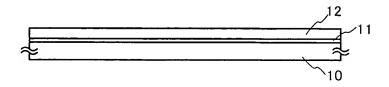


Fig. 3B irradiation of strong light

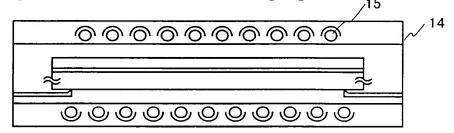


Fig. 3C laser anneal

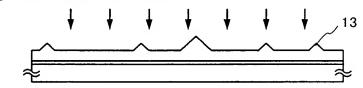


Fig. 3D heat treatment process

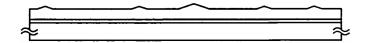
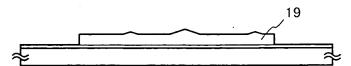


Fig. 3E formation of semiconductor film



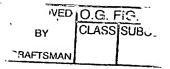


Fig. 4A formation of conductive film/formation of insulating film /formation of semiconductor film

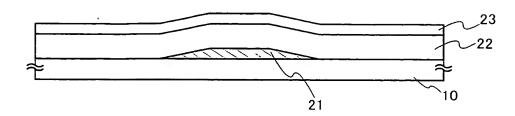


Fig. 4B laser anneal

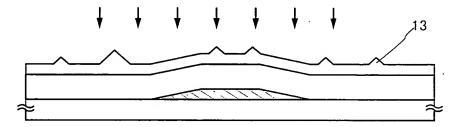


Fig. 4C heat treatment process

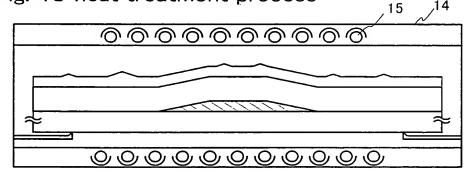
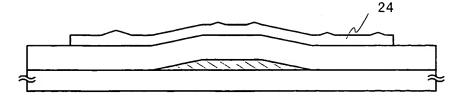
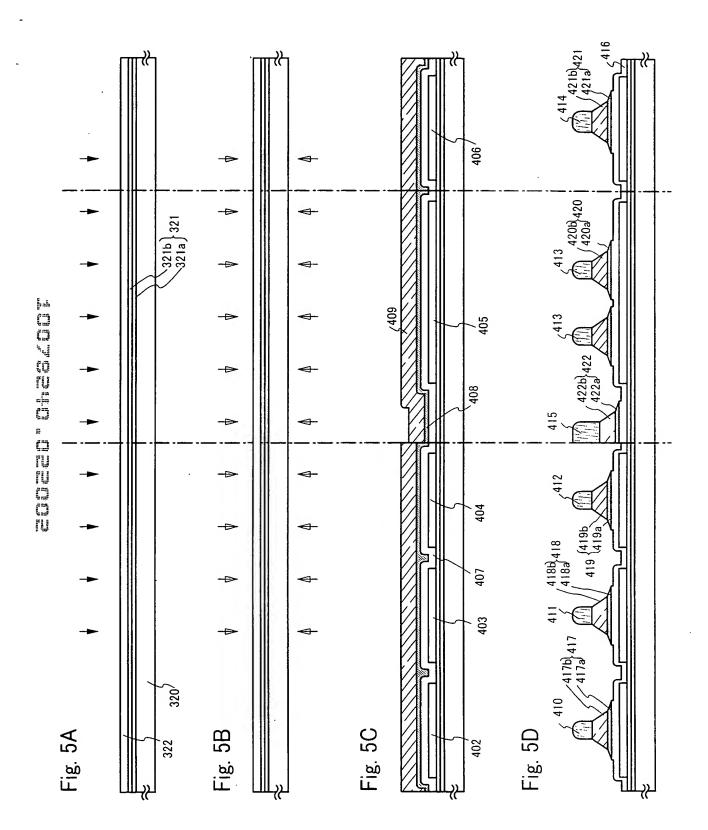
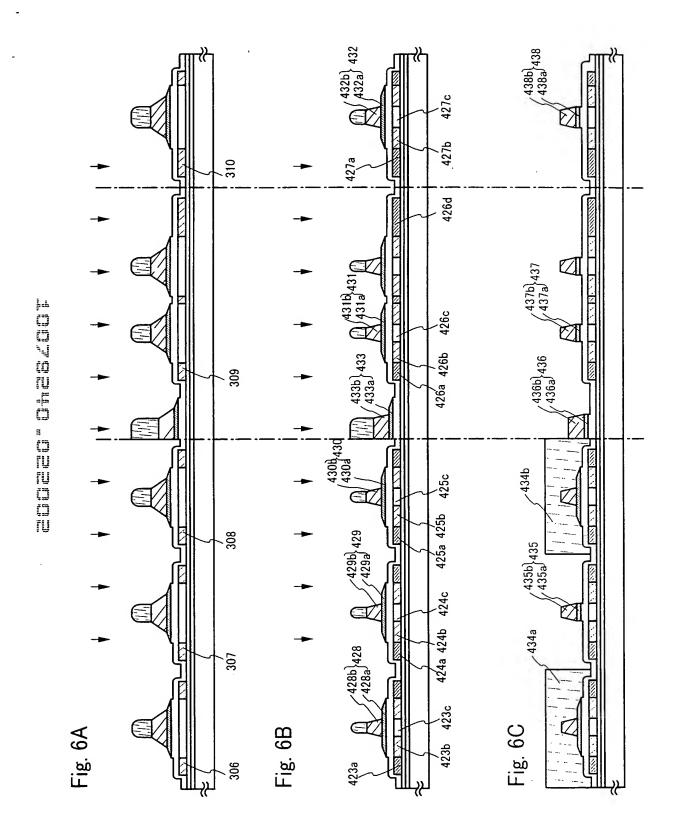


Fig. 4D formation of semiconductor film







446a 446b 446c 446d Fig. 7C Fig. 7A Fig. 7B

Fig. 8

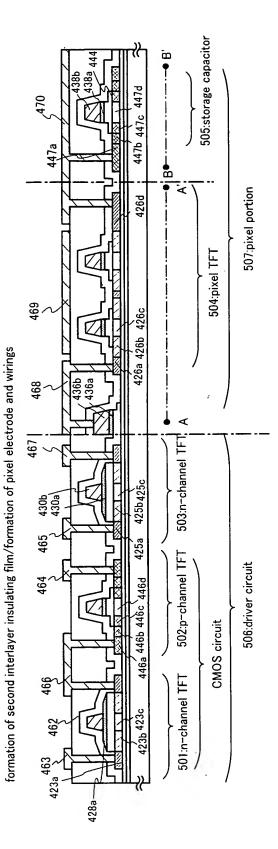


Fig. 9

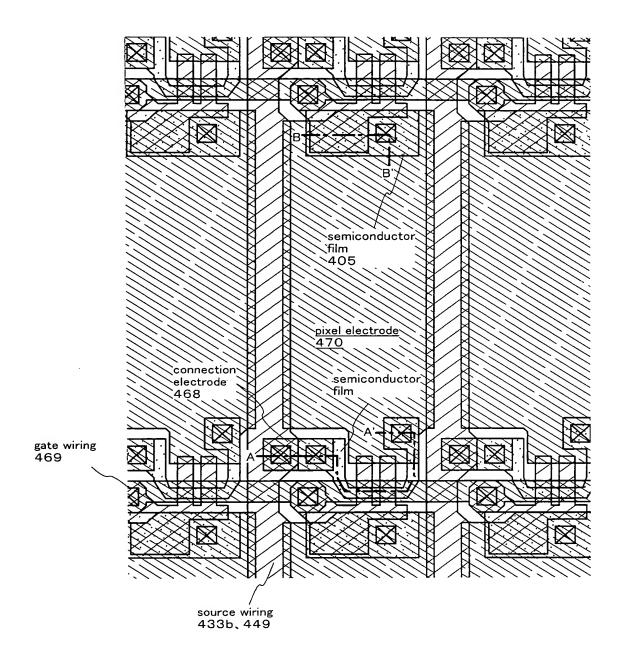


Fig. 10

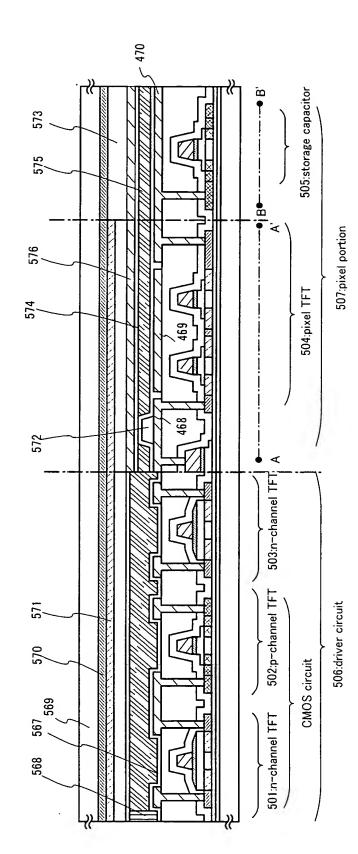


Fig. 11

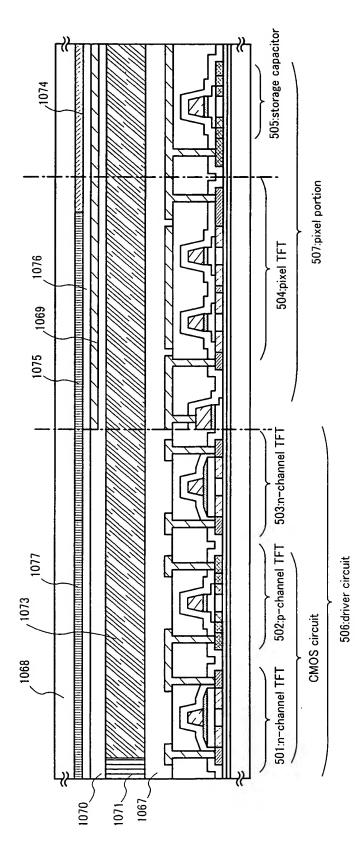
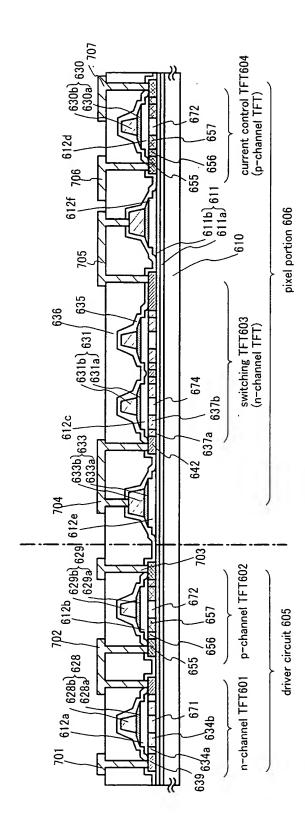
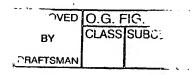
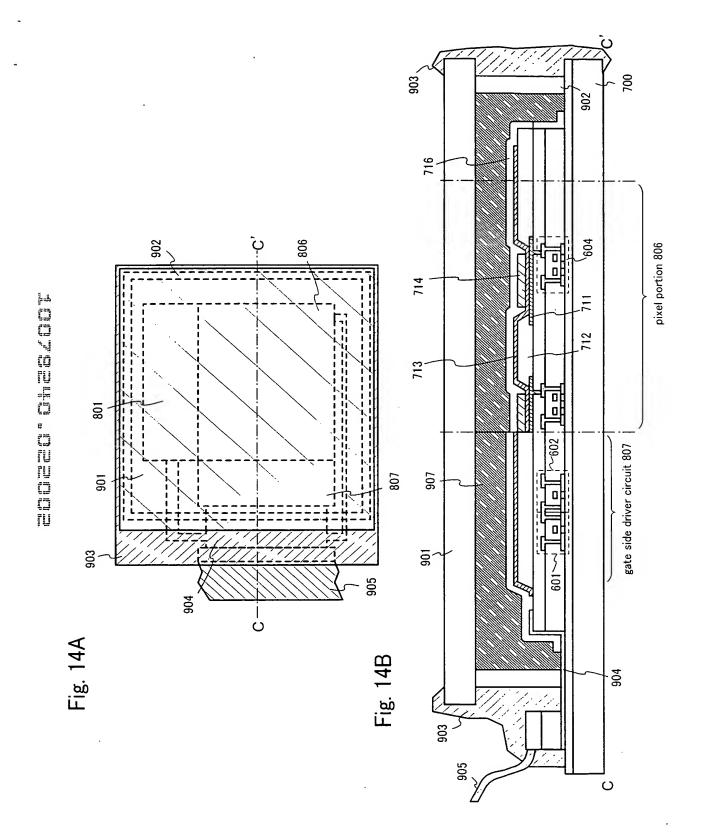


Fig. 12



current control TFT604 (p-channel TFT) 657 pixel portion 606 switching TFT603 (n-channel TFT) 711 713 714 674 637a 710 703 p-channel TFT602 718 driver circuit 605 702 n-channel TFT601 712 701





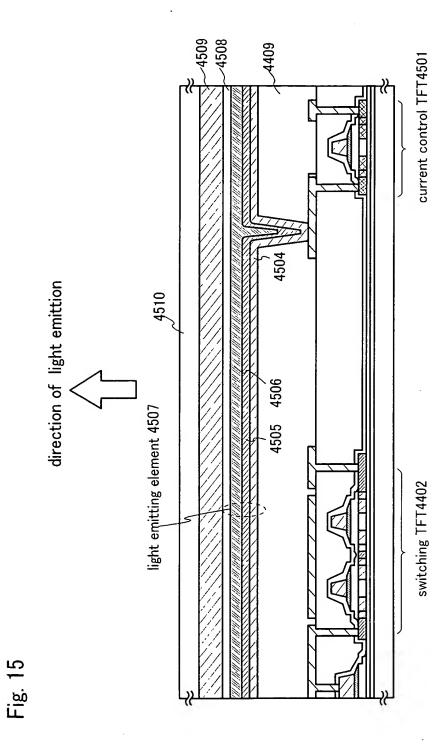
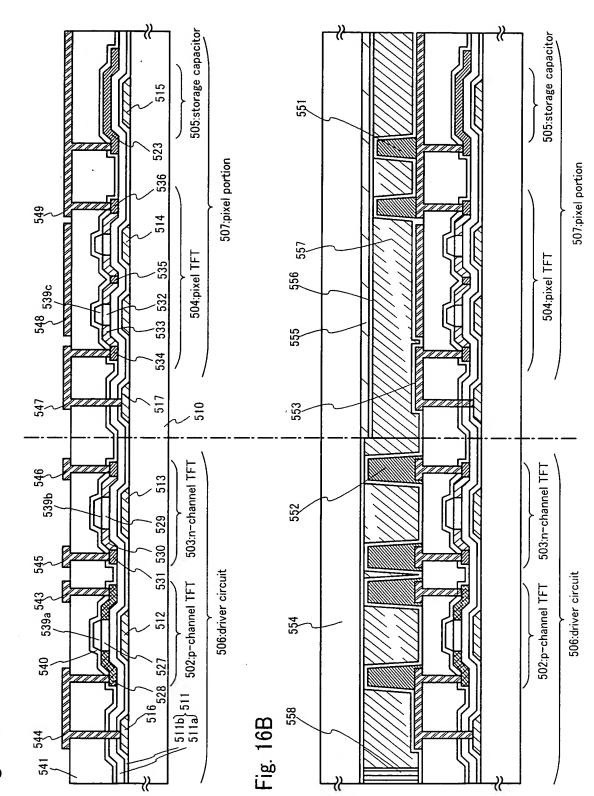
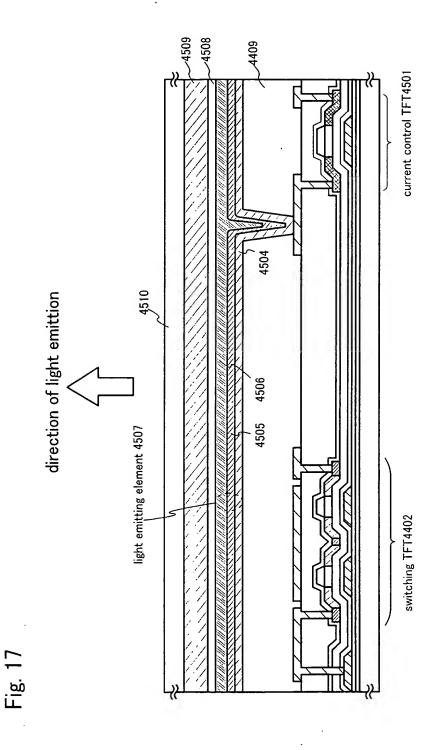


Fig. 16A

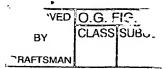


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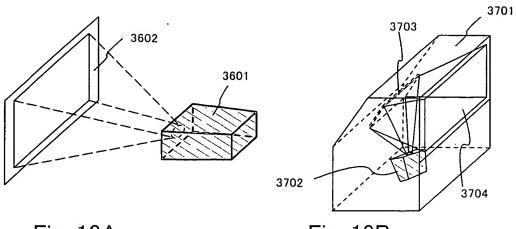


Fig. 19A

Fig. 19B

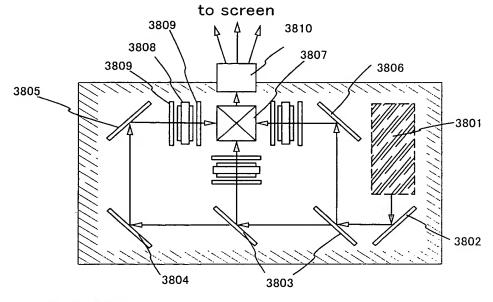


Fig. 19C

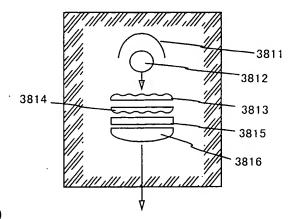


Fig. 19D



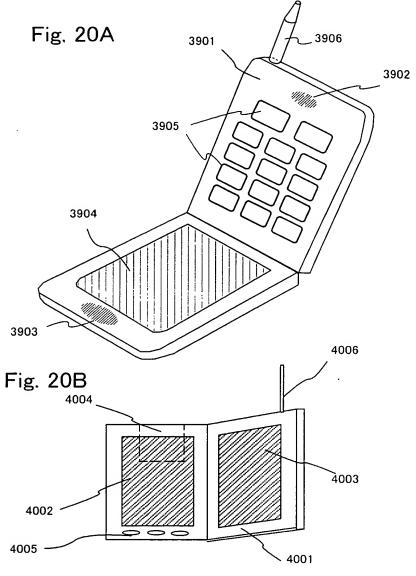


Fig. 20C